

N-Channel Enhancement Mode MOSFET with Schottky Diode

Features

MOSFET

- 20V/3A,
 $R_{DS(ON)} = 50m\Omega (typ.) @ V_{GS} = 4.5V$
 $R_{DS(ON)} = 80m\Omega (typ.) @ V_{GS} = 2.5V$
- Super High Dense Cell Design
- Reliable and Rugged
- Lead Free and Green Devices Available
 (RoHS Compliant)

SBD

- Low Forward Voltage

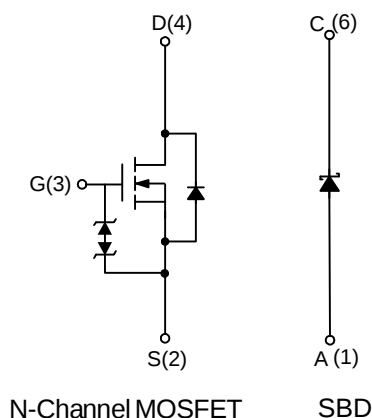
Applications

- Power Management in Notebook Computer, Portable Equipment and Battery Powered Systems.

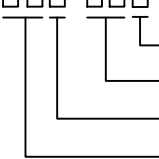
Pin Description



Top View of JSOT-6



Ordering and Marking Information

APM2802 □□□-□□□ 	Package Code CG : JSOT-6 Operating Junction Temperature Range C : -55 to 150 °C Handling Code TR : Tape & Reel Assembly Material G : Halogen and Lead Free Device
APM2802 CG : M2802 XXXXX	XXXXXX - Date Code

Note: ANPEC lead-free products contain molding compounds/die attach materials and 100% matte tin plate termination finish; which are fully compliant with RoHS. ANPEC lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J-STD-020C for MSL classification at lead-free peak reflow temperature. ANPEC defines "Green" to mean lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

ANPEC reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Unit
MOSFET			
V_{DSS}	Drain-Source Voltage	20	V
V_{GSS}	Gate-Source Voltage	± 10	
I_D^*	Continuous Drain Current	$V_{GS}=4.5V$	A
I_{DM}^*	300 μs Pulsed Drain Current		
I_S^*	Diode Continuous Forward Current	1	A
T_J	Maximum Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	
P_D^*	Maximum Power Dissipation	$T_A=25^\circ\text{C}$	W
		$T_A=100^\circ\text{C}$	
$R_{\theta JA}^*$	Thermal Resistance-Junction to Ambient	150	$^\circ\text{C/W}$
SBD			
V_{RRM}	Repetitive Peak Reverse Voltage	20	V
I_{FSM}	Maximum Peak Forward Surge Current	5.5	A

Note : *Surface Mounted on 1in² pad area, $t \leq 10\text{sec}$.

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	APM2802CG			Unit
			Min.	Typ.	Max.	
MOSFET						
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	20	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =16V, V _{GS} =0V	-	-	1	μA
		T _J =85°C	-	-	30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	0.45	0.6	1	V
I _{GSS}	Gate Leakage Current	V _{GS} =±10V, V _{DS} =0V	-	-	±10	μA
R _{DS(ON)} ^a	Drain-Source On-state Resistance	V _{GS} =4.5V, I _{DS} =3A	-	50	70	mΩ
		V _{GS} =2.5V, I _{DS} =1.7A	-	80	110	
V _{SD} ^a	Diode Forward Voltage	I _{SD} =0.5A, V _{GS} =0V	-	0.7	1.3	V

Electrical Characteristics (Cont.) ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	APM2802CG			Unit
			Min.	Typ.	Max.	
MOSFET						
Dynamic Characteristics ^b						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =10V, Frequency=1.0MHz	-	270	-	pF
C _{oss}	Output Capacitance		-	80	-	
C _{rss}	Reverse Transfer Capacitance		-	50	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =10V, R _L =10Ω, I _{DS} =1A, V _{GEN} =4.5V, R _G =6Ω	-	4	8	ns
T _r	Turn-on Rise Time		-	10	19	
t _{d(OFF)}	Turn-off Delay Time		-	20	37	
T _f	Turn-off Fall Time		-	4	8	
t _{rr}	Reverse Recovery Time	I _{DS} =3A, dI _{SD} /dt=100A/μs	-	17	-	ns
Q _{rr}	Reverse Recovery Charge		-	7	-	nC
Gate Charge Characteristics ^b						
Q _g	Total Gate Charge	V _{DS} =10V, V _{GS} =4.5V, I _{DS} =3A	-	4	6	nC
Q _{gs}	Gate-Source Charge		-	0.6	-	
Q _{gd}	Gate-Drain Charge		-	1.6	-	
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V _R	Reverse Voltage	I _R =0.5mA	20	-	-	V
V _{F1}	Forward Voltage	I _F =10mA	-	-	0.4	V
V _{F2}		I _F =500mA	-	-	0.5	V
I _R	Reverse Current	V _R =15V	-	-	200	μA
C ^b	Junction Capacitance	V _R =10V, Frequency=1.0MHz	-	45	-	pF

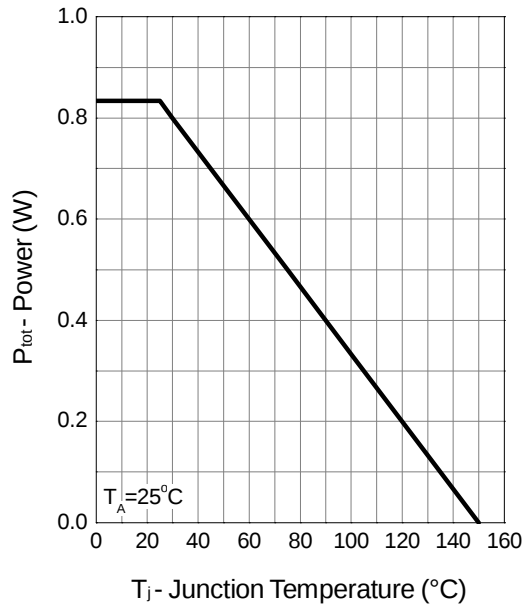
Note a : Pulse test ; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

Note b : Guaranteed by design, not subject to production testing.

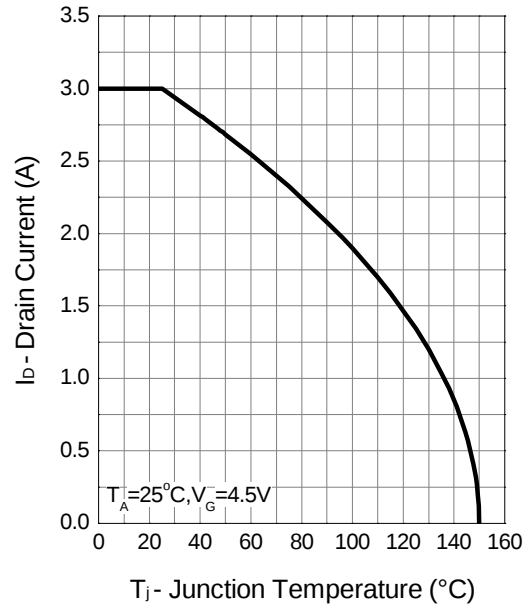
Typical Operating Characteristics

N-Channel MOSFET

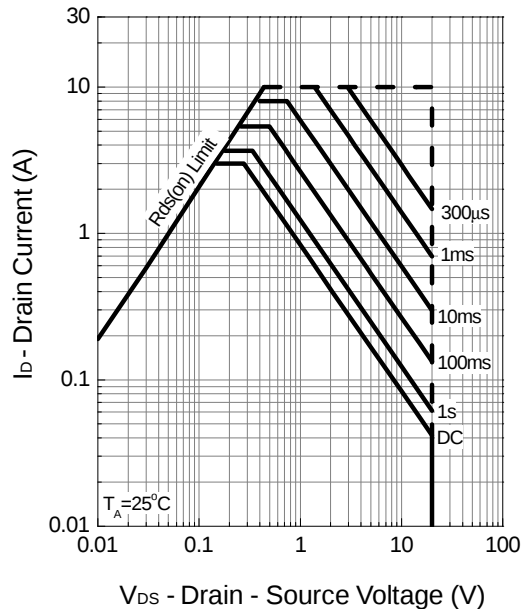
Power Dissipation



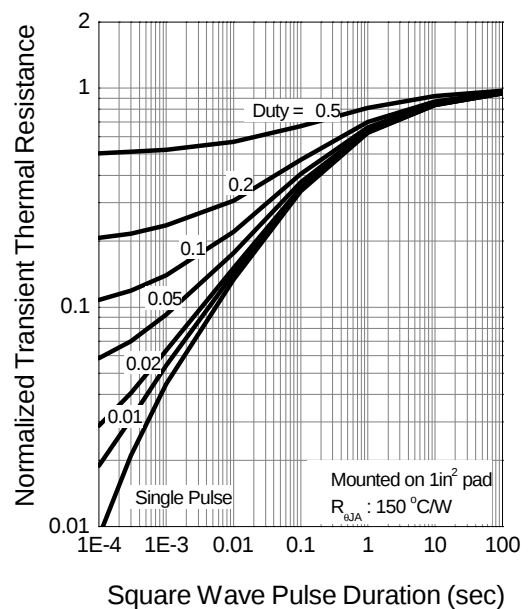
Drain Current



Safe Operation Area



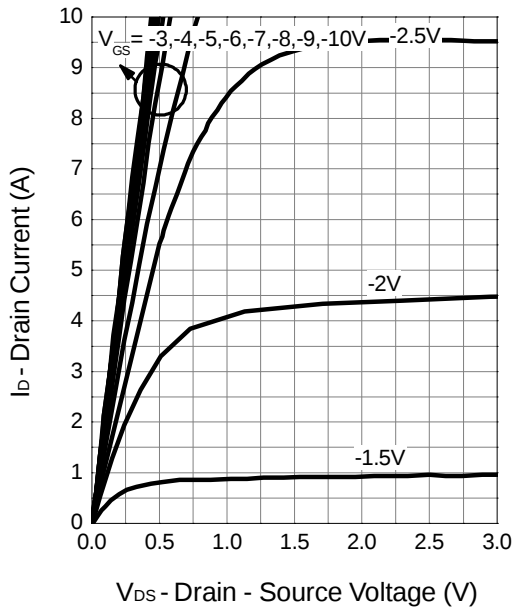
Thermal Transient Impedance



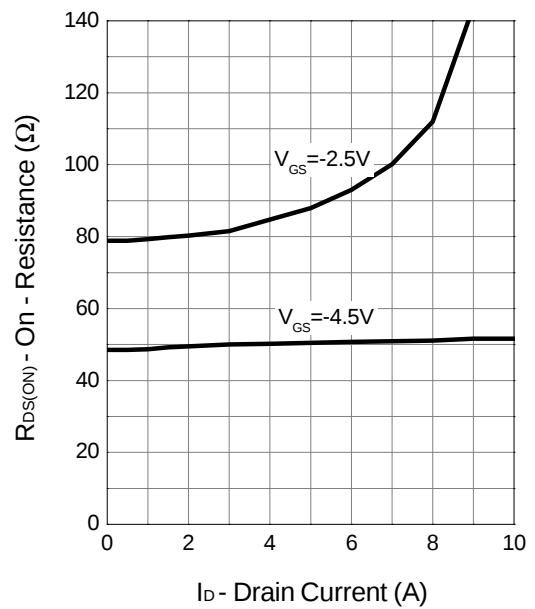
Typical Operating Characteristics (Cont.)

N-Channel MOSFET

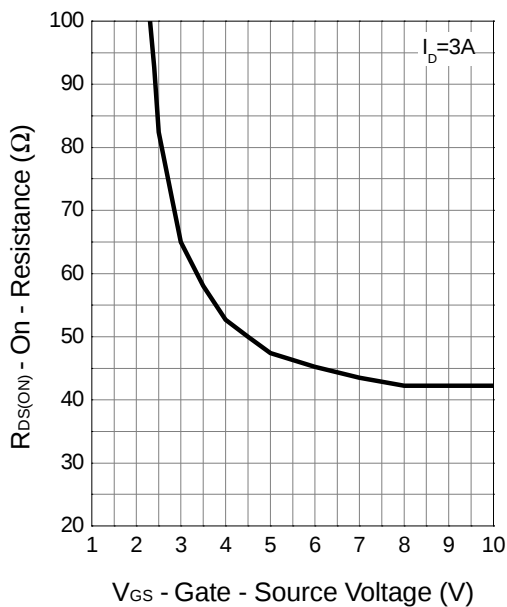
Output Characteristics



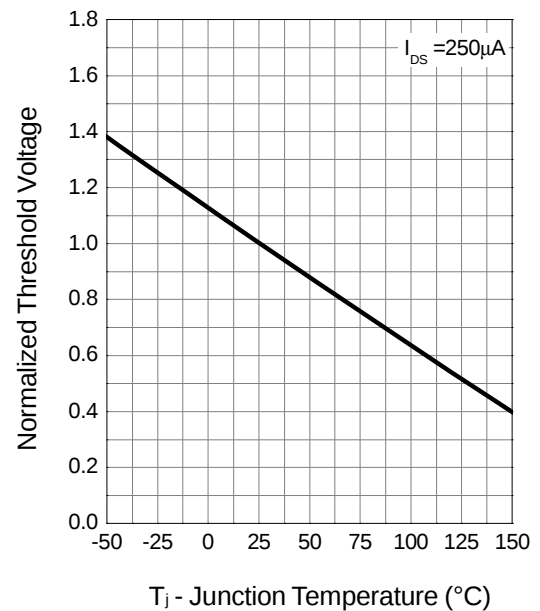
Drain-Source On Resistance



Drain-Source On Resistance



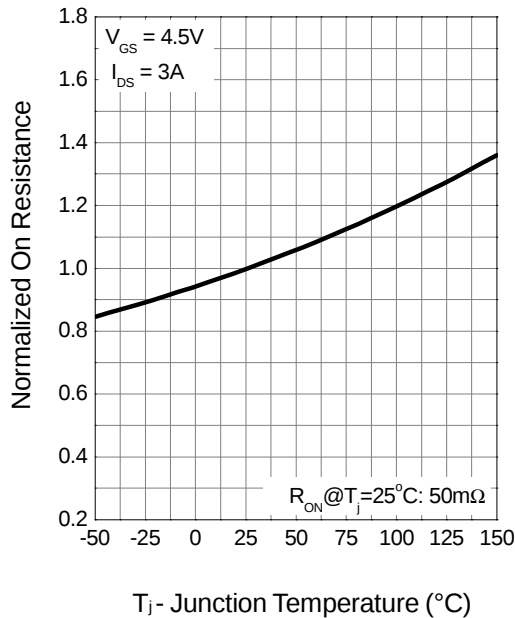
Gate Threshold Voltage



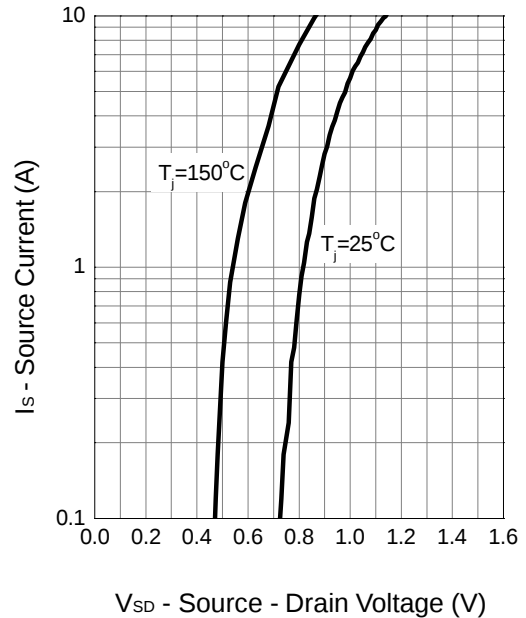
Typical Operating Characteristics (Cont.)

N-Channel MOSFET

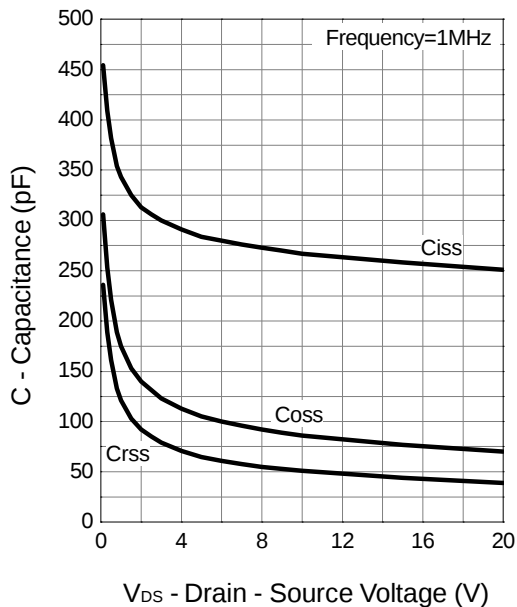
Drain-Source On Resistance



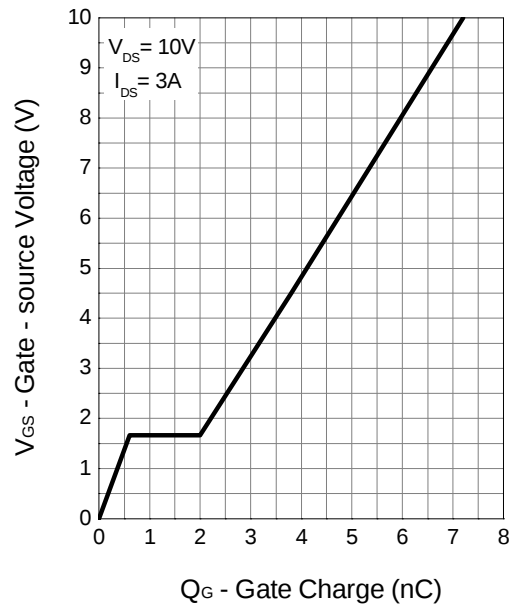
Source-Drain Diode Forward



Capacitance

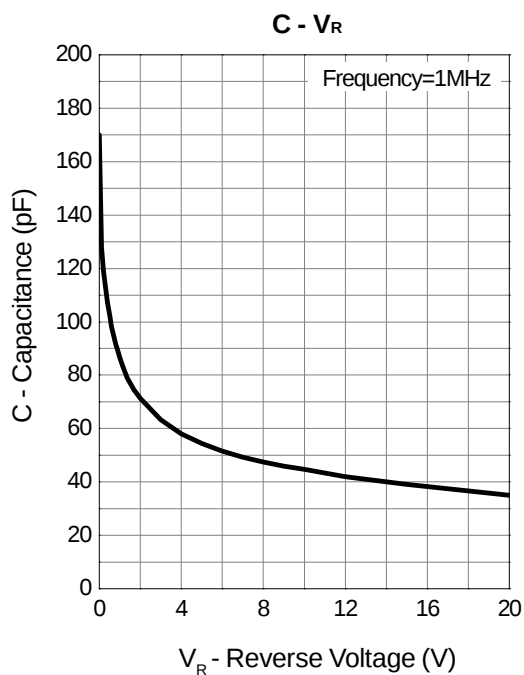
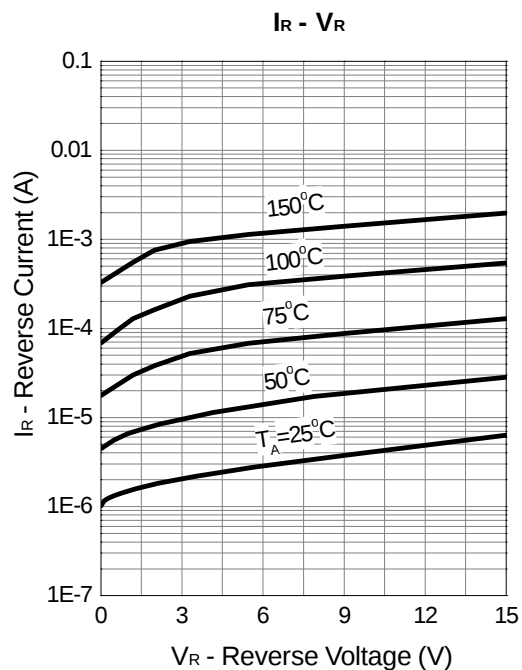
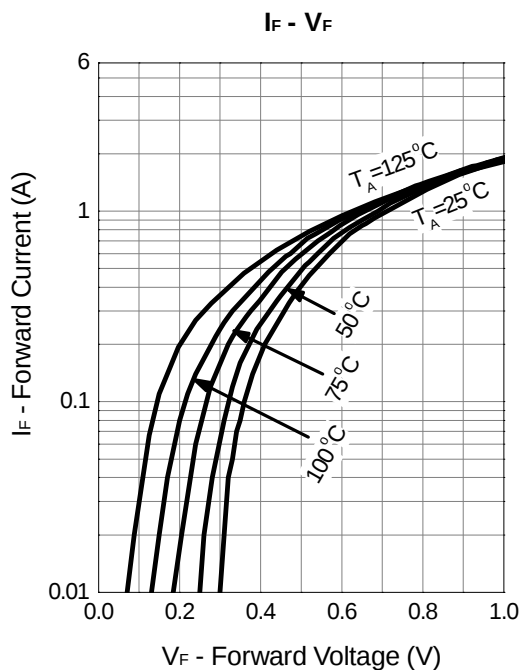


Gate Charge



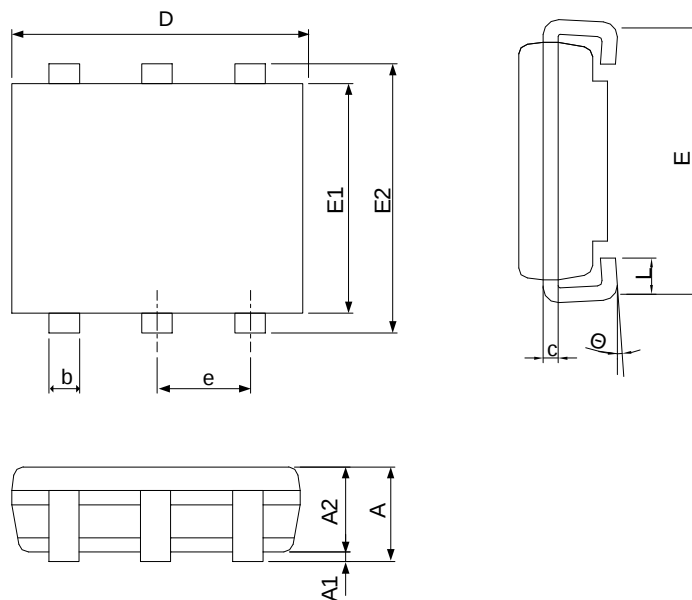
Typical Operating Characteristics (Cont.)

SBD



Package Information

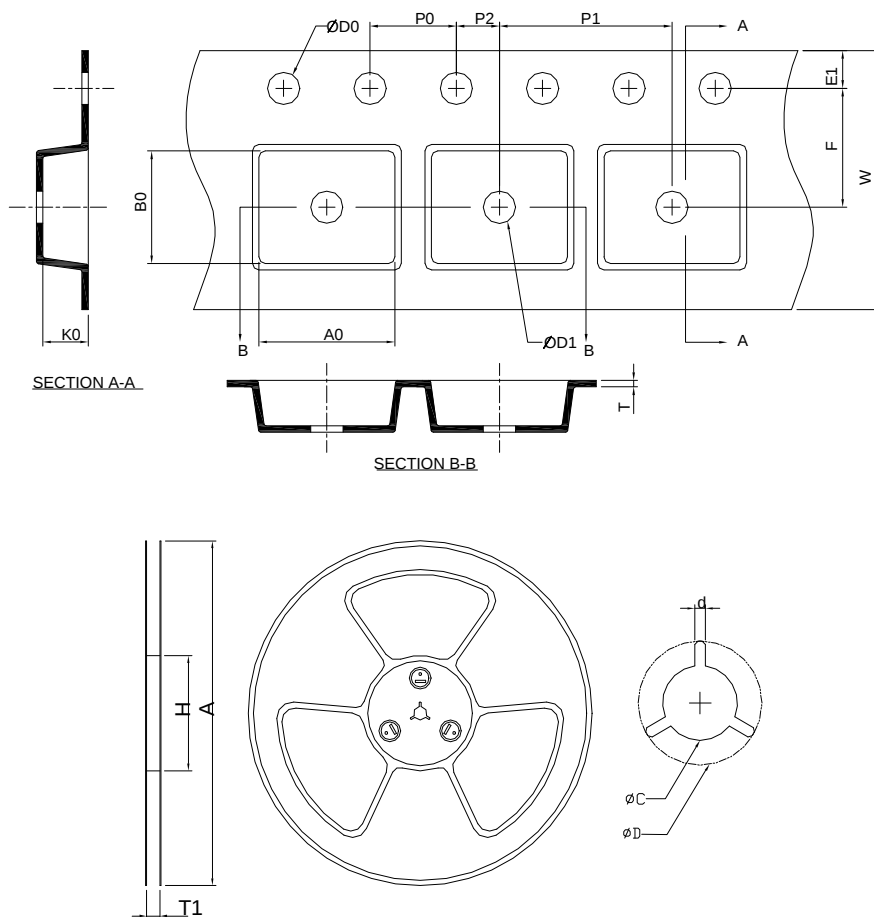
JSOT-6



DIMENSIONS	JSOT-6			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.93	1.10	0.037	0.043
A1	0.01	0.10	0.000	0.004
A2	0.92	1.00	0.036	0.039
b	0.25	0.40	0.010	0.016
c	0.10	0.20	0.004	0.008
D	2.95	3.10	0.116	0.122
E	2.50	3.00	0.098	0.118
E1	2.30	2.50	0.091	0.098
E2	2.65	3.05	0.104	0.120
e	0.95 BSC		0.037 BSC	
θ	0°	8°	0°	8°
L	0.30	0.60	0.012	0.024

Note : 1. Follow GEM 2928 6J.
2. Dimension D, D1, and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 10 mil.

Carrier Tape & Reel Dimensions



Application	A	H	T1	C	d	D	W	E1	F
JSOT-6	178.0 $\pm$ 2.00	50 MIN.	8.4+2.00 -0.00	13.0+0.50 -0.20	1.5 MIN.	20.2 MIN.	8.0 $\pm$ 0.30	1.75 $\pm$ 0.10	3.5 $\pm$ 0.05
	P0	P1	P2	D0	D1	T	A0	B0	K0
	4.0 $\pm$ 0.10	4.0 $\pm$ 0.10	2.0 $\pm$ 0.05	1.5+0.10 -0.00	1.0 MIN.	0.6+0.00 -0.40	3.20 $\pm$ 0.20	3.10 $\pm$ 0.20	1.50 $\pm$ 0.20

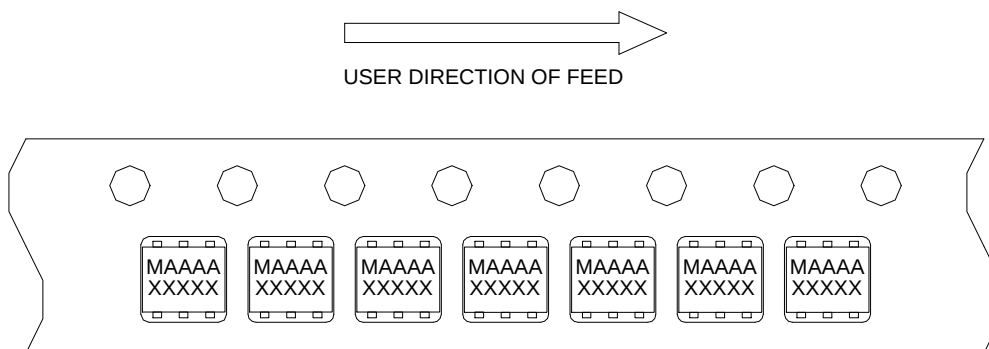
(mm)

Devices Per Unit

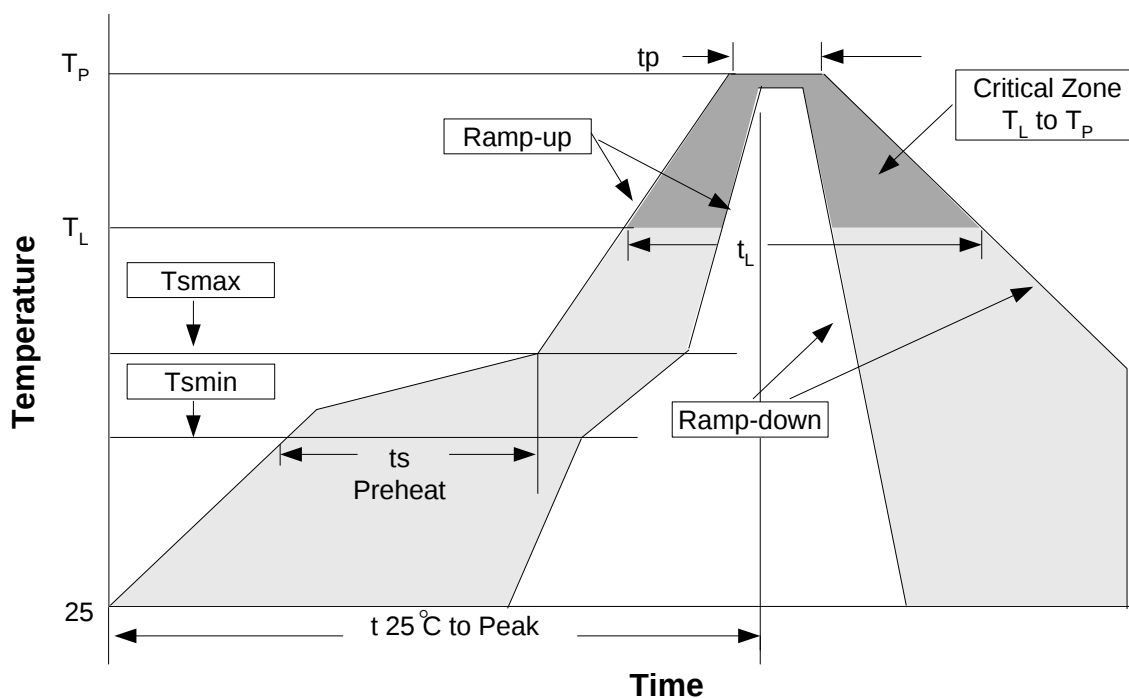
Package Type	Unit	Quantity
JSOT-6	Tape & Reel	3000

Taping Direction Information

JSOT-6



Reflow Condition (IR/Convection or VPR Reflow)



Reliability Test Program

Test item	Method	Description
SOLDERABILITY	MIL-STD-883D-2003	245°C, 5 sec
HOLT	MIL-STD-883D-1005.7	1000 Hrs Bias @125°C
PCT	JESD-22-B, A102	168 Hrs, 100%RH, 121°C
TST	MIL-STD-883D-1011.9	-65°C~150°C, 200 Cycles

Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	3°C/second max.	3°C/second max.
Preheat - Temperature Min (T_{smin}) - Temperature Max (T_{smax}) - Time (min to max) (ts)	100°C 150°C 60-120 seconds	150°C 200°C 60-180 seconds
Time maintained above: - Temperature (T_L) - Time (t_L)	183°C 60-150 seconds	217°C 60-150 seconds
Peak/Classification Temperature (T_P)	See table 1	See table 2
Time within 5°C of actual Peak Temperature (t_P)	10-30 seconds	20-40 seconds
Ramp-down Rate	6°C/second max.	6°C/second max.
Time 25°C to Peak Temperature	6 minutes max.	8 minutes max.

Note: All temperatures refer to topside of the package. Measured on the body surface.

Table 1. SnPb Eutectic Process – Package Peak Reflow Temperatures

Package Thickness	Volume mm ³ <350	Volume mm ³ 350
<2.5 mm	240 +0/-5°C	225 +0/-5°C
≥2.5 mm	225 +0/-5°C	225 +0/-5°C

Table 2. Pb-free Process – Package Classification Reflow Temperatures

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 +0°C*	260 +0°C*	260 +0°C*
1.6 mm – 2.5 mm	260 +0°C*	250 +0°C*	245 +0°C*
≥2.5 mm	250 +0°C*	245 +0°C*	245 +0°C*

*Tolerance: The device manufacturer/supplier **shall** assure process compatibility up to and including the stated classification temperature (this means Peak reflow temperature +0°C. For example 260°C+0°C) at the rated MSL level.

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